

Fig. 1 PRIOR ART

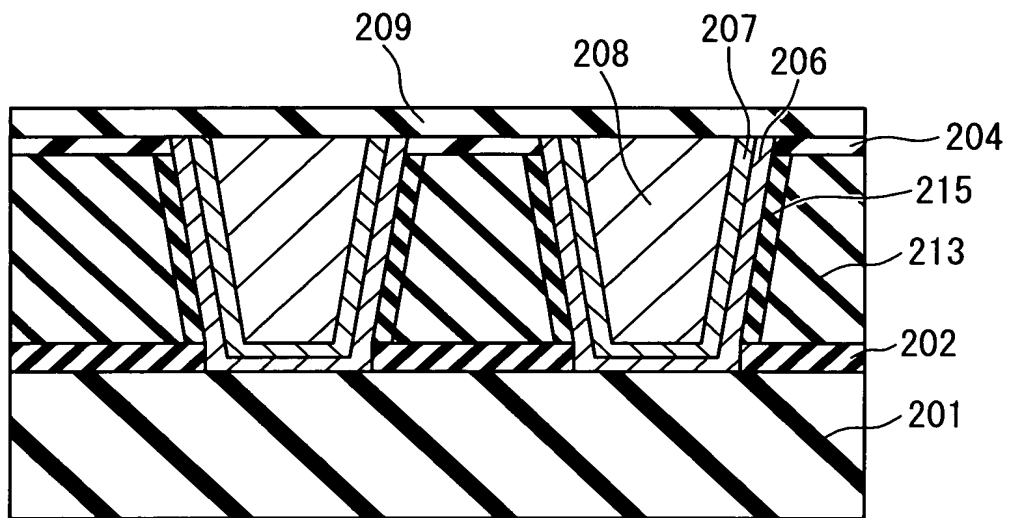


Fig. 2A PRIOR ART

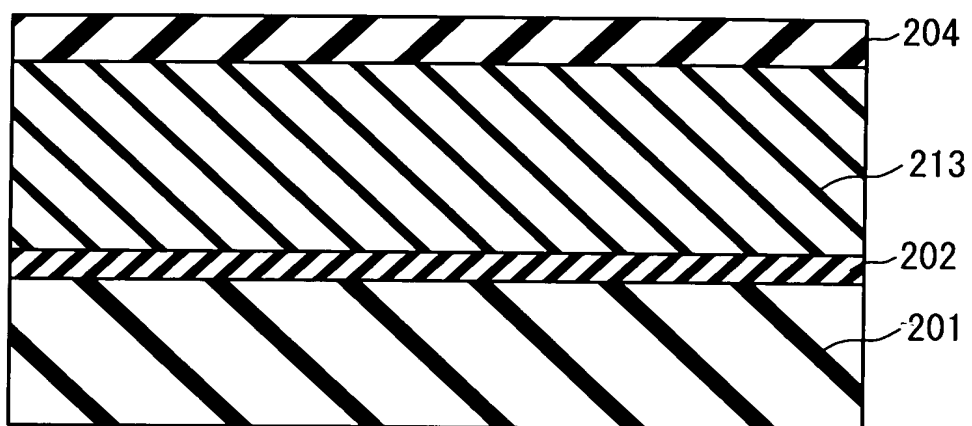
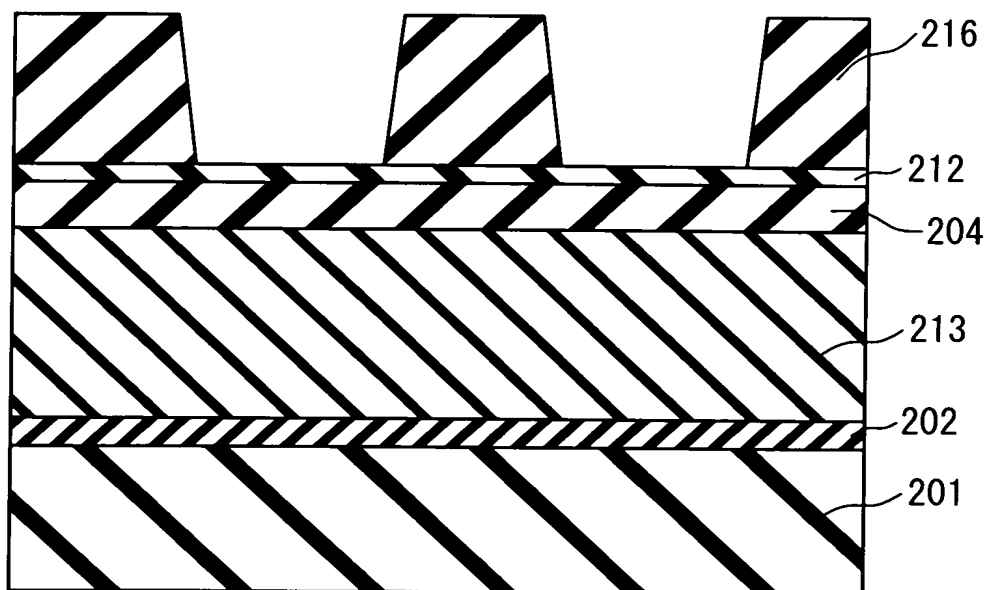


Fig. 2B PRIOR ART



A cross-sectional view of a semiconductor device. It features a base layer 201 with diagonal hatching. On top of this base are three pillars. Each pillar has a bottom layer 202 with horizontal hatching, a middle layer 213 with diagonal hatching, and a top layer 204 with horizontal hatching. The side surfaces of the pillars are labeled 215. The gaps between the pillars are labeled 220.

Fig. 3A PRIOR ART

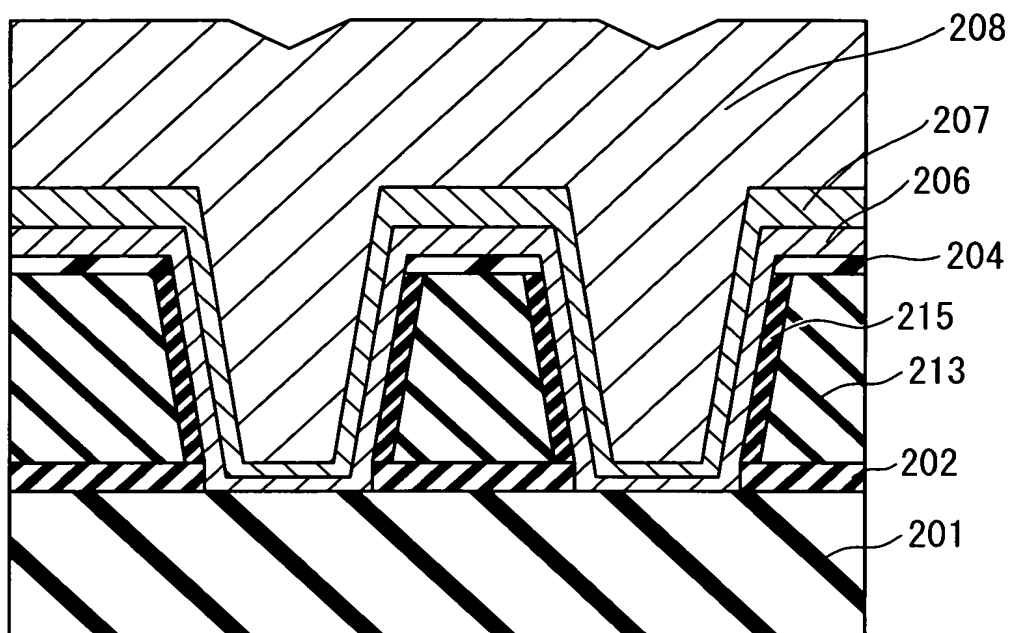


Fig. 3B PRIOR ART

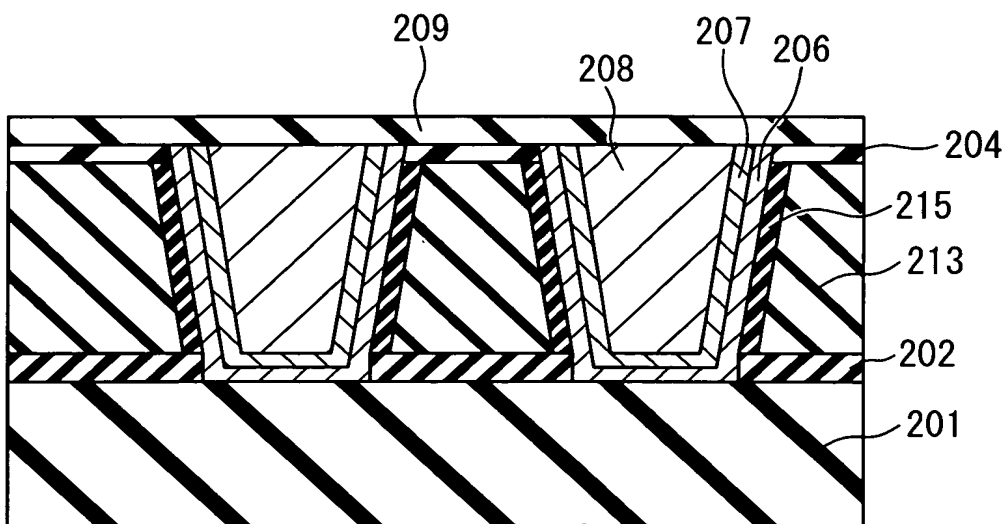


Fig. 4

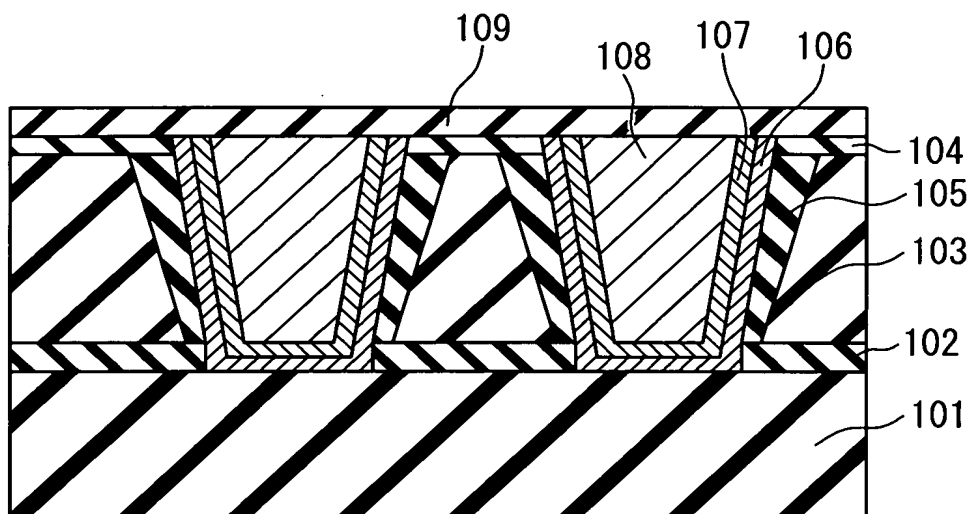


Fig. 5A

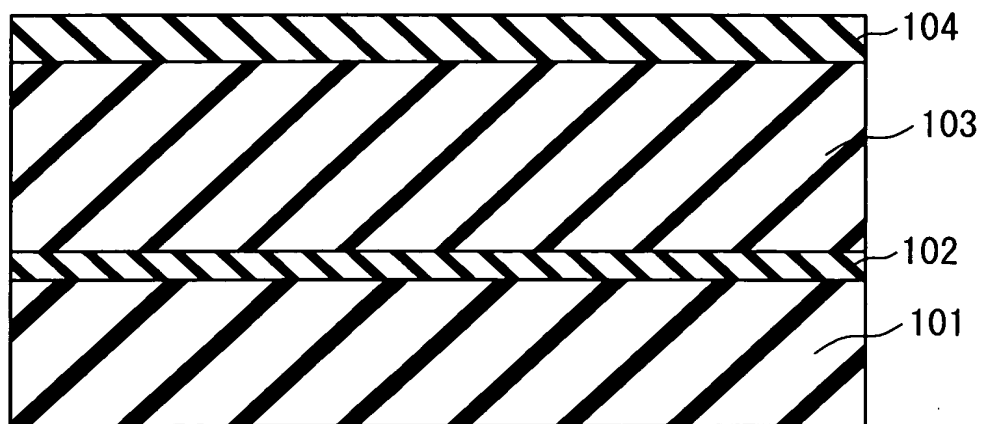


Fig. 5B

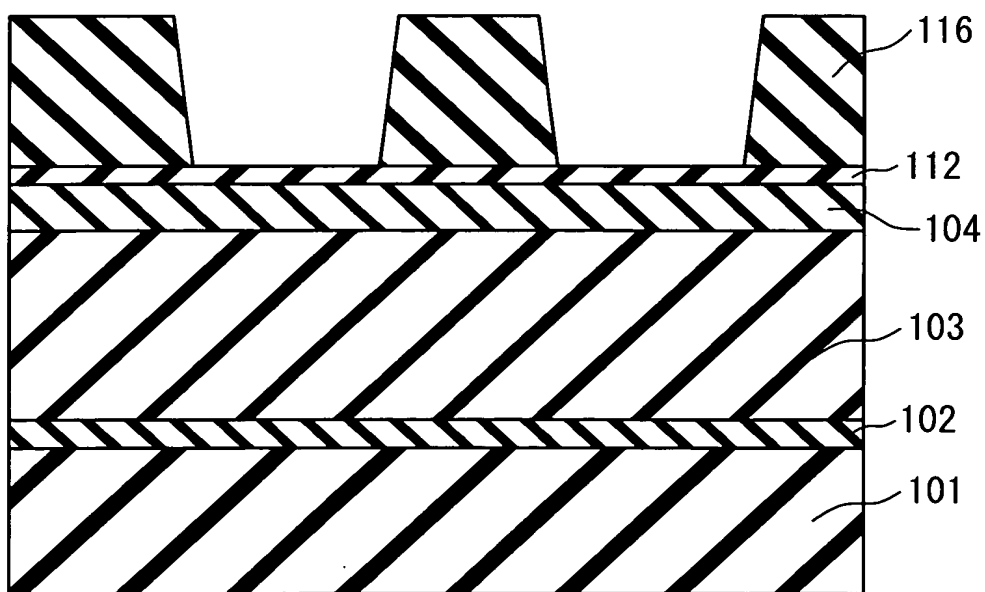


Fig. 5C

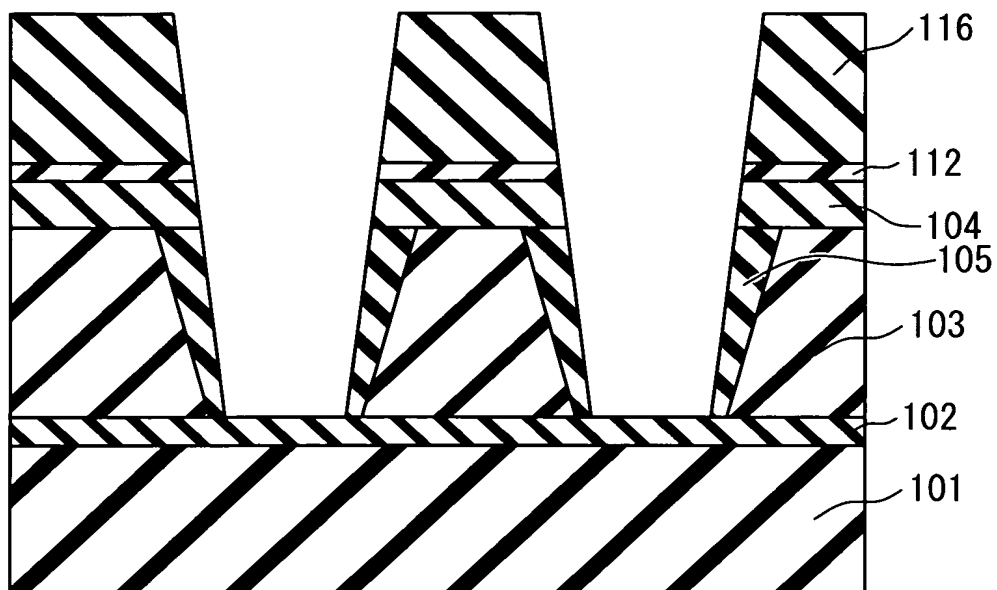


Fig. 5D

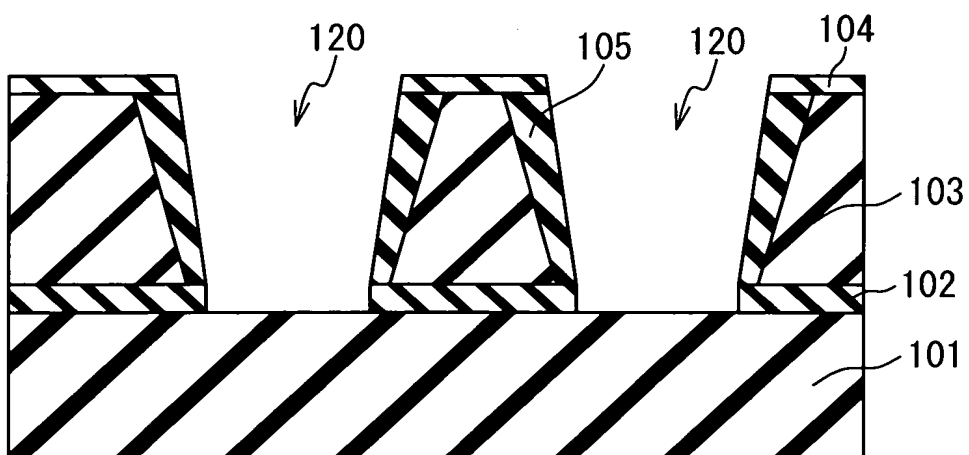


Fig. 6A

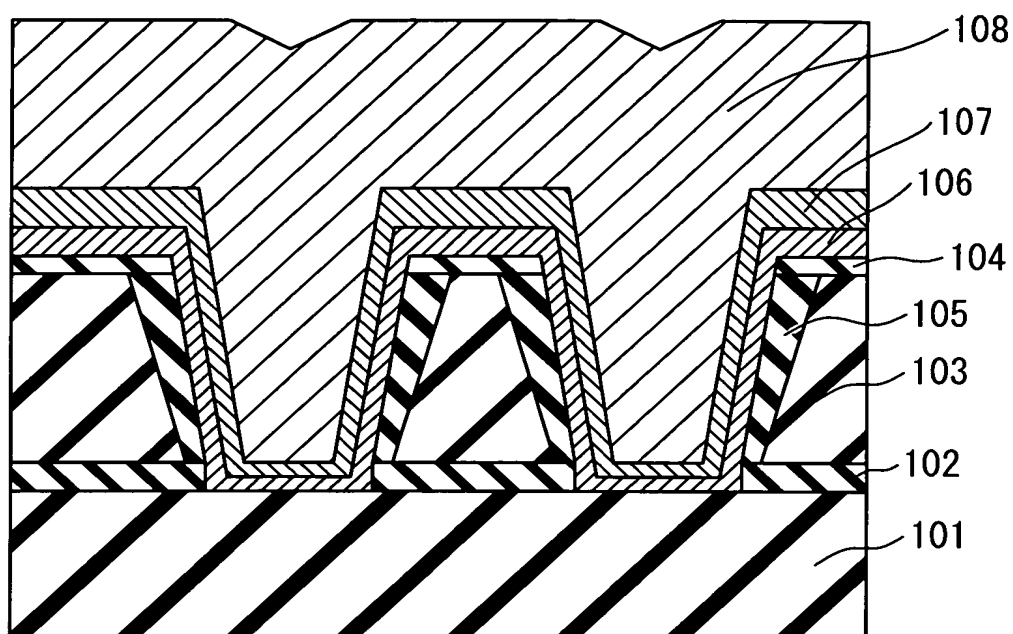


Fig. 6B

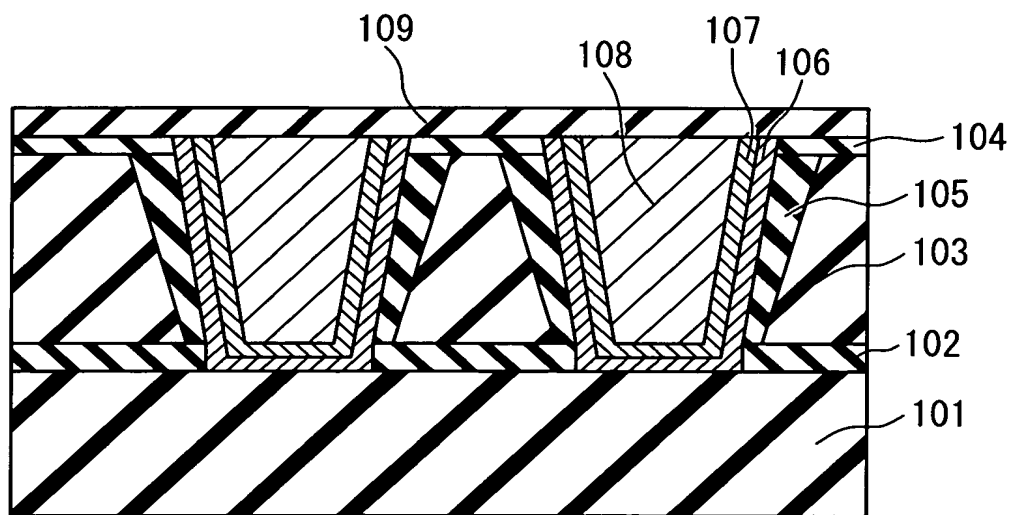




Fig. 7

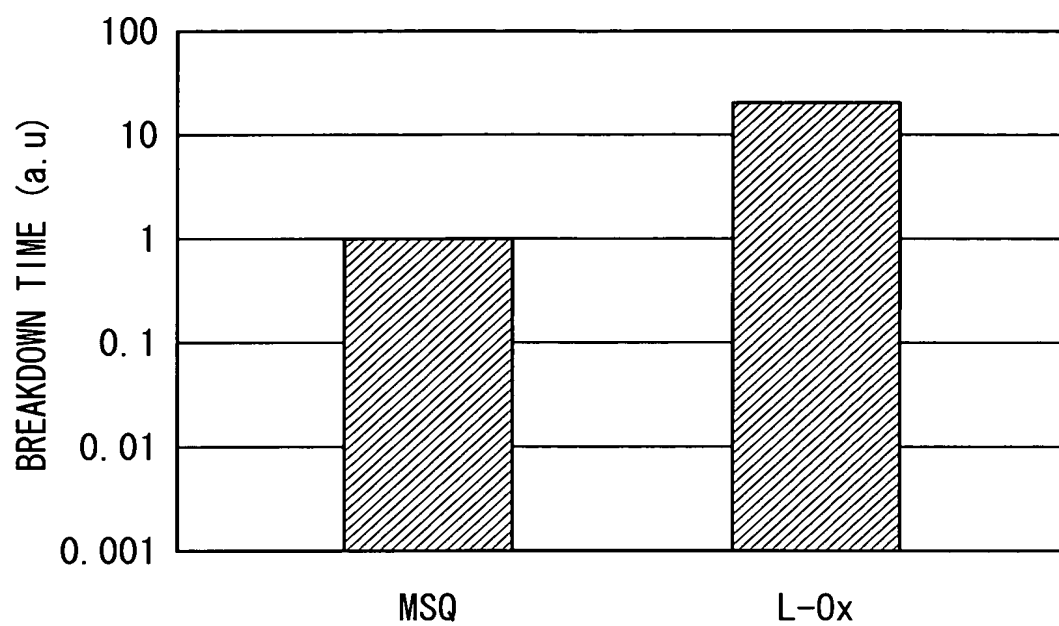


Fig. 8

